

BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G, SBC857BDW1T1G Series, BC858CDW1T1G Series



ON Semiconductor®

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Dual General Purpose Transistors

PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------|-------------------|------|
| Collector-Emmitter Voltage BC856, SBC856 BC857, SBC857 BC858 | V_{CEO} | -65 -45 -30 | V |
| Collector-Base Voltage BC856, SBC856 BC857, SBC857 BC858 | V_{CBO} | -80 -50 -30 | V |
| Emitter-Base Voltage | V_{EBO} | -5.0 | V |
| Collector Current -Continuous | I_C | -100 | mAdc |
| Collector Current - Peak | I_C | -200 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|-------------------|----------------------------------|
| Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C | P_D | 380 250 3.0 | mW mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 328 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

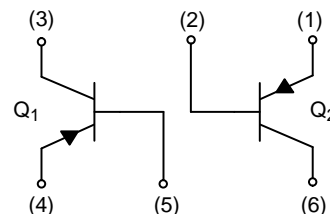
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in

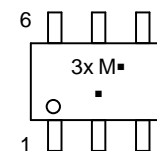
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



SOT-363/SC-88
CASE 419B
STYLE 1



MARKING DIAGRAM



- 3x = Specific Device Code
x = B, F, G, or L
(See Ordering Information)
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

**BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G,
SBC857BDW1T1G Series, BC858CDW1T1G Series**

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|---------------|----------------------|-----|-------------|---------------------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$) BC856, SBC856 Series BC857, SBC857 Series BC858 Series | $V_{(BR)CEO}$ | -65 -45 -30 | - | - | V |
| Collector–Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$) BC856, SBC856 Series BC857B, SBC857B Only BC858 Series | $V_{(BR)CES}$ | -80 -50 -30 | - | - | V |
| Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$) BC856, SBC856 Series BC857, SBC857 Series BC858 Series | $V_{(BR)CBO}$ | -80 -50 -30 | - | - | V |
| Emitter–Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$) BC856, SBC856 Series BC857, SBC857 Series BC858 Series | $V_{(BR)EBO}$ | -5.0 -5.0 -5.0 | - | - | V |
| Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$) | I_{CBO} | - | - | -15 -4.0 | nA μA |

ON CHARACTERISTICS

| | | | | | |
|---|---------------|----------------------|--------------------------|----------------------|---|
| DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$) BC856B, SBC856B, BC857B, SBC857B BC857C, SBC857C, BC858C ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) BC856B, SBC856B, BC857B, SBC857B BC857C, SBC857C, BC858C | h_{FE} | - - 220 420 | 150 270 290 520 | - - 475 800 | - |
| Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{CE(sat)}$ | - - | - - | -0.3 -0.65 | V |
| Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$) | $V_{BE(sat)}$ | - - | -0.7 -0.9 | - - | V |
| Base–Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$) | $V_{BE(on)}$ | -0.6 - | - - | -0.75 -0.82 | V |

SMALL– SIGNAL CHARACTERISTICS

| | | | | | |
|--|----------|-----|---|-----|-----|
| Current–Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$) | f_T | 100 | - | - | MHz |
| Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$) | C_{ob} | - | - | 4.5 | pF |
| Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$) | NF | - | - | 10 | dB |

**BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G,
SBC857BDW1T1G Series, BC858CDW1T1G Series**

TYPICAL CHARACTERISTICS – BC856/SBC856



Figure 1. DC Current Gain



Figure 2. "On" Voltage



Figure 3. Collector Saturation Region



Figure 4. Base-Emitter Temperature Coefficient



Figure 5. Capacitance



Figure 6. Current-Gain - Bandwidth Product

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TYPICAL CHARACTERISTICS – BC857/SBC857/BC858



Figure 7. Normalized DC Current Gain



Figure 8. "Saturation" and "On" Voltages



Figure 9. Collector Saturation Region



Figure 10. Base-Emitter Temperature Coefficient



Figure 11. Capacitances



Figure 12. Current-Gain - Bandwidth Product

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Figure 13. Thermal Response



Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

**BC856BDW1T1G, SBC856BDW1T1G Series, BC857BDW1T1G,
SBC857BDW1T1G Series, BC858CDW1T1G Series**

ORDERING INFORMATION

| Device | Device Marking | Package | Shipping [†] |
|---------------|----------------|----------------------|-----------------------|
| BC856BDW1T1G | 3B | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC856BDW1T1G | 3B | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC856BDW1T3G | 3B | SOT-363 (Pb-Free) | 10,000 / Tape & Reel |
| SBC856BDW1T3G | 3B | SOT-363 (Pb-Free) | 10,000 / Tape & Reel |
| BC857BDW1T1G | 3F | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC857BDW1T1G | 3F | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC857CDW1T1G | 3G | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| SBC857CDW1T1G | 3G | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |
| BC858CDW1T1G | 3L | SOT-363 (Pb-Free) | 3,000 / Tape & Reel |

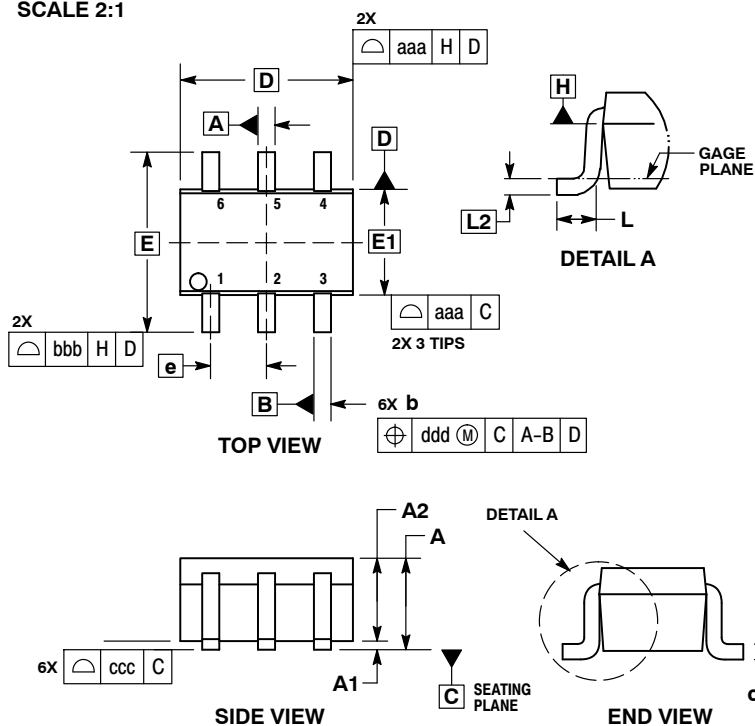
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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SCALE 2:1

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

DATE 11 DEC 2012



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|-----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | --- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC | | | 0.026 BSC | | |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC | | | 0.006 BSC | | |
| aaa | 0.15 | | | 0.006 | | |
| bbb | 0.30 | | | 0.012 | | |
| ccc | 0.10 | | | 0.004 | | |
| ddd | 0.10 | | | 0.004 | | |

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y

DATE 11 DEC 2012

| | | | | | |
|---|---|--|--|--|--|
| STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2 | STYLE 2: CANCELLED | STYLE 3: CANCELLED | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2 |
| STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2 | STYLE 8: CANCELLED | STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2 | STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2 | STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2 | STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2 |
| STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE | STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC | STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1 | STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1 | STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1 | STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1 |
| STYLE 19: PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF | STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR | STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1 | STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c) | STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C | STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE |
| STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1 | STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1 | STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2 | STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN | STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE | STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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